Elektronische Bauelemente

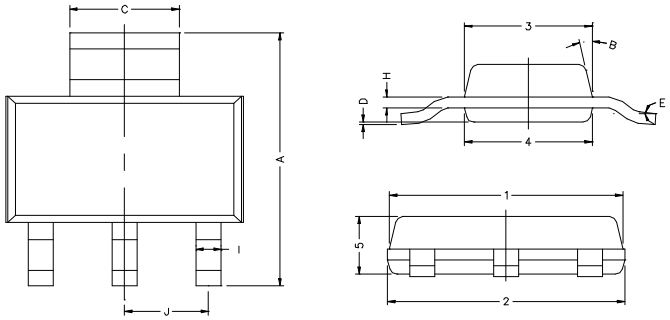
PZT965

NPN Transistor

Epitaxial Planar Transistor

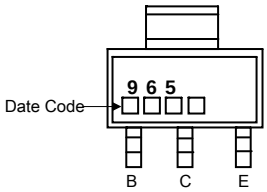
RoHS Compliant Product

SOT-223



Description

The PZT965 is designed for use as AF output amplifier and flash unit.



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.70	7.30	B	13°TYP.	
C	2.90	3.10	J	2.30 REF.	
D	0.02	0.10	1	6.30	6.70
E	0°	10°	2	6.30	6.70
I	0.60	0.80	3	3.30	3.70
H	0.25	0.35	4	3.30	3.70
			5	1.40	1.80

ABSOLUTE MAXIMUM RATINGS Ta=25°C

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	20	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current (Continous)	5	A
	Collector Current (Peak PT=10mS)	8	
P_D	Total Power Dissipation	2	W
T_J,T_{stg}	Junction and Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS Tamb=25°C unless otherwise specified

Parameter	Symbol	Min	Typ.	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV_{CBO}	40	-	-	V	I_C= 100μA
Collector-Emitter Breakdown Voltage	*BV_{CEO}	20	-	-	V	I_C= 1mA
Emitter-Base Breakdown Voltage	BV_{EBO}	7	-	-	V	I_E= 10μA
Collector-Base Cutoff Current	I_{CBO}	-	-	0.1	uA	V_{CB}= 60V
Emitter-Base Cutoff Current	I_{EBO}	-	-	0.1	uA	V_{EB}=7V
Collector Saturation Voltage	*V_{CE}(sat)	-	0.35	1	V	I_C=3A,I_B=0.1A
DC Current Gain	*h_{FE}1	230	-	800		V_{CE}= 2V, I_C=0.5A
	*h_{FE}2	150	-	-		V_{CE}= 2V, I_C=2A
Gain-Bandwidth Product	fT	-	150	-	MHz	V_{CE}= 6V, I_E= 50mA
Output Capacitance	C_{ob}	-	-	50	pF	V_{CB}= 20V, f=1MHz

*Pulse width≦300μs, Duty Cycle≦2%

Classification of hFE

Rank	R
Range	340~600

Characteristics Curve